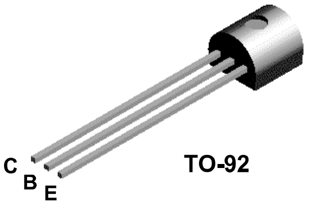
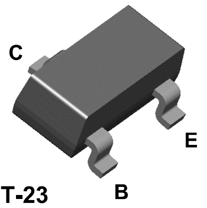
FAIRCHILD
SEMICONDUCTOR ™

2N5401 MMBT5401



TO-92



SOT-23
Mark: 2L

PNP General Purpose Amplifier

This device is designed as a general purpose amplifier and switch for applications requiring high voltages.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	150	V
V_{CBO}	Collector-Base Voltage	160	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	600	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5401	***MMBT5401**	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."